

# MOSFET – N-Channel, POWERTRENCH®

30 V, 15 A, 7.0 mΩ

## FDS8817NZ, FDS8817NZ-G

### General Description

This N-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process that has been especially tailored to minimize the on-state resistance.

This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

### Features

- Max  $r_{DS(on)}$  = 7 mΩ at  $V_{GS}$  = 10 V,  $I_D$  = 15 A
- Max  $r_{DS(on)}$  = 10 mΩ at  $V_{GS}$  = 4.5 V,  $I_D$  = 12.6 A
- HBM ESD Protection Level of 3.8 kV Typical\*
- High Performance Trench Technology for Extremely Low  $r_{DS(on)}$
- High Power and Current Handling Capability
- These Devices are Pb-Free and are RoHS Compliant

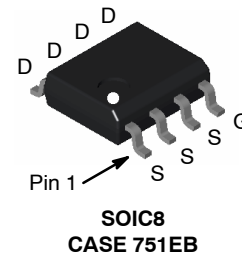
### Specifications

#### MOSFET MAXIMUM RATINGS ( $T_A$ = 25°C unless otherwise noted)

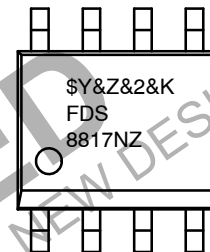
Symbol	Parameter		Ratings	Unit
V <sub>DS</sub>	Drain to Source Voltage		30	V
V <sub>GS</sub>	Gate to Source Voltage		±20	V
I <sub>D</sub>	Drain Current	Continuous (Note 1a)	15	A
		Pulsed	60	
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 2)		181	mJ
P <sub>D</sub>	Power Dissipation	(Note 1a)	2.5	W
		(Note 1b)	1.0	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

\*The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

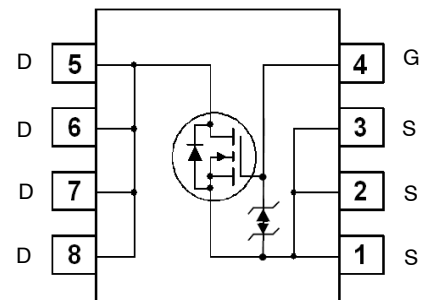


### MARKING DIAGRAM



\$Y = onsemi Logo  
 &Z = Assembly Plant Code  
 &2 = Numeric Date Code  
 &K = Lot Code  
 FDS8817NZ = Specific Device Code

### PIN ASSIGNMENT



### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	25	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	125	

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a.  $50^{\circ}\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b.  $125^{\circ}\text{C/W}$  when mounted on a minimum pad

2. Starting  $T_J = 25^{\circ}\text{C}$ ;  $L = 3\text{ mH}$ ,  $I_{AS} = 11\text{ A}$ ,  $V_{DD} = 30\text{ V}$ ,  $V_{GS} = 10\text{ V}$ .

**DISCONTINUED**  
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN  
PLEASE CONTACT YOUR onsemi  
REPRESENTATIVE FOR INFORMATION

# FDS8817NZ, FDS8817NZ-G

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V	30			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, referenced to 25°C		20		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μA

### ON CHARACTERISTICS (Note 3)

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	1	1.8	3	V
ΔV <sub>GS(th)</sub> / ΔT <sub>J</sub>	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, referenced to 25°C		-6		mV/°C
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		5.4	7	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 12.6 A		7.0	10	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125°C		7.5	11	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 15 A		54		S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1805	2400	pF
C <sub>oss</sub>	Output Capacitance			335	445	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			200	300	pF
R <sub>g</sub>	Gate Resistance	f = 1 MHz		1.4		Ω

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 15 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω		11	22	ns
t <sub>r</sub>	Rise Time			13	26	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			25	40	ns
t <sub>f</sub>	Fall Time			7	14	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = 0 V to 10 V, V <sub>DD</sub> = 15 V, I <sub>D</sub> = 15 A		32	45	nC
		V <sub>GS</sub> = 0 V to 5 V, V <sub>DD</sub> = 15 V, I <sub>D</sub> = 15 A		17	24	nC
Q <sub>gs</sub>	Gate to Source Charge	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 15 A		6		nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge			7		nC

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.1 A (Note 3)		0.8	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 15 A, di/dt = 100 A/μs		24	36	ns
Q <sub>rr</sub>	Reverse Recovery Charge			15	23	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

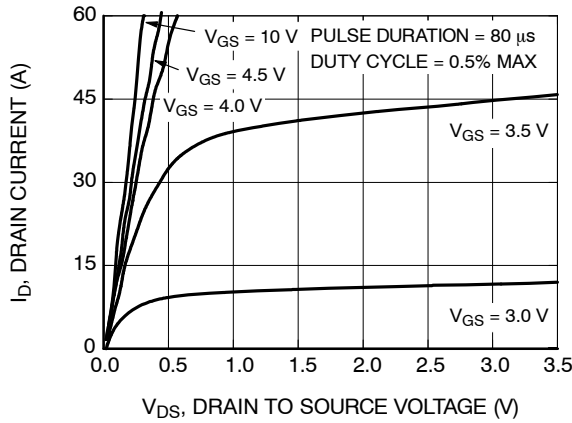


Figure 1. On Region Characteristics

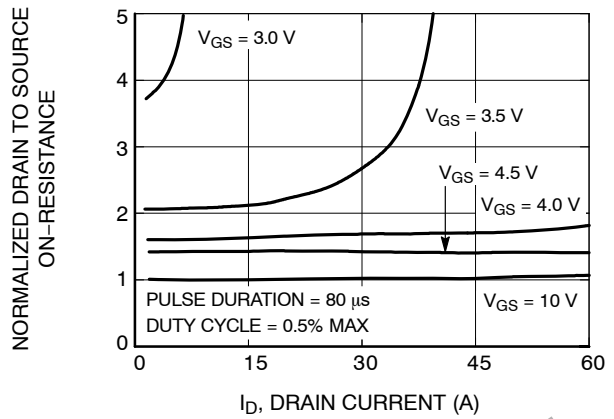


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

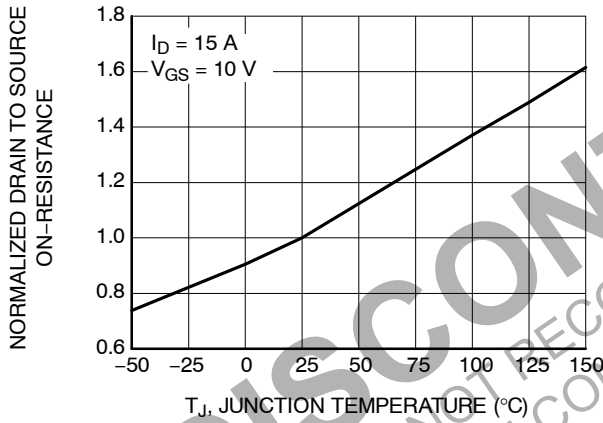


Figure 3. Normalized On Resistance vs. Junction Temperature

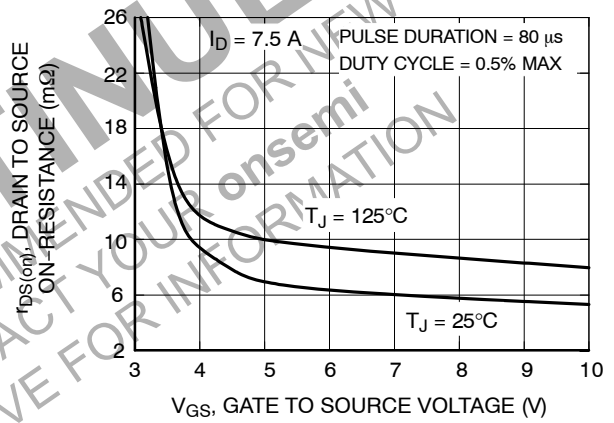


Figure 4. On-Resistance vs. Gate to Source Voltage

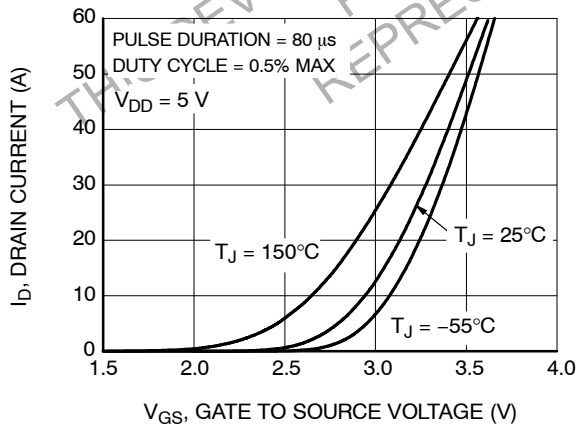


Figure 5. Transfer Characteristics

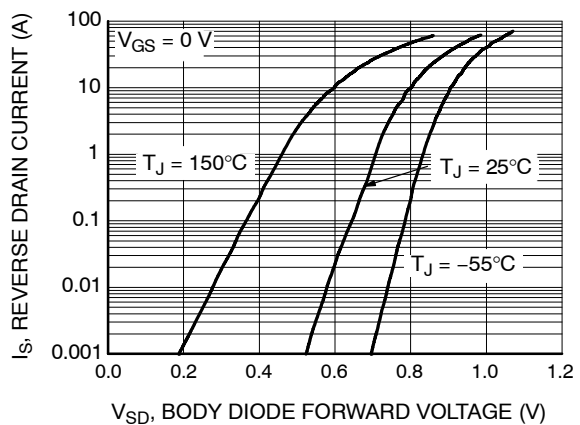


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted) (continued)

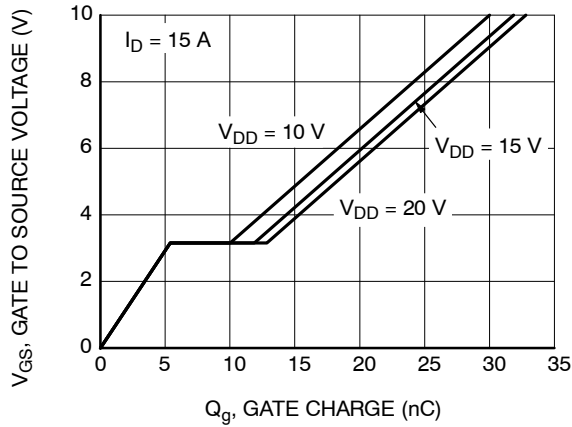


Figure 7. Gate Charge Characteristics

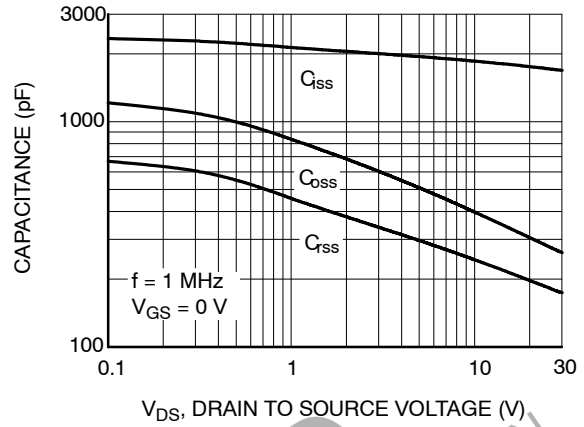


Figure 8. Capacitance vs. Drain to Source Voltage

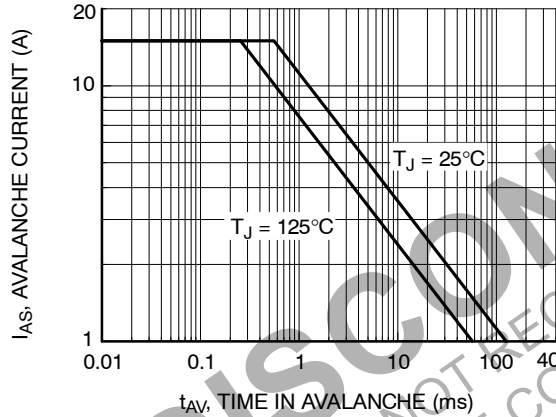


Figure 9. Unclamped Inductive Switching Capability

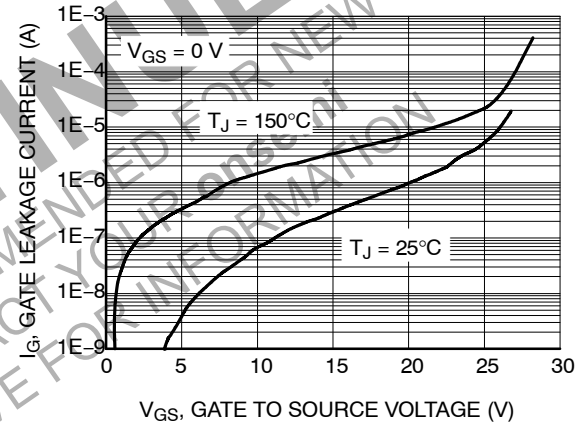


Figure 10. Gate Leakage Current vs. Gate to Source Voltage

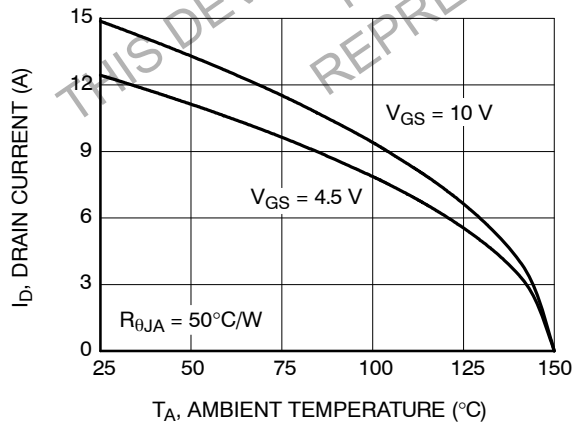


Figure 11. Maximum Continuous Drain Current vs. Ambient Temperature

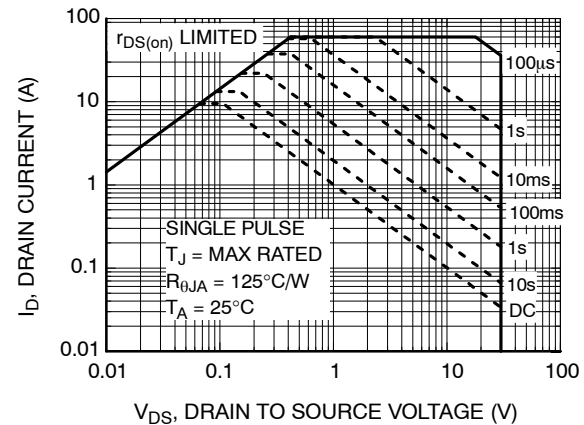


Figure 12. Forward Bias Safe Operating Area

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted) (continued)

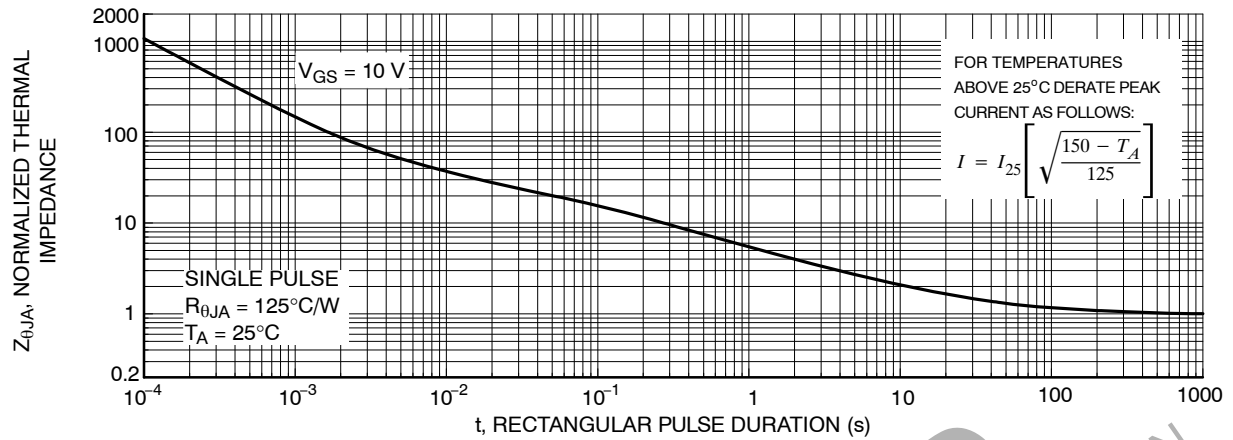


Figure 13. Single Pulse Maximum Power Dissipation

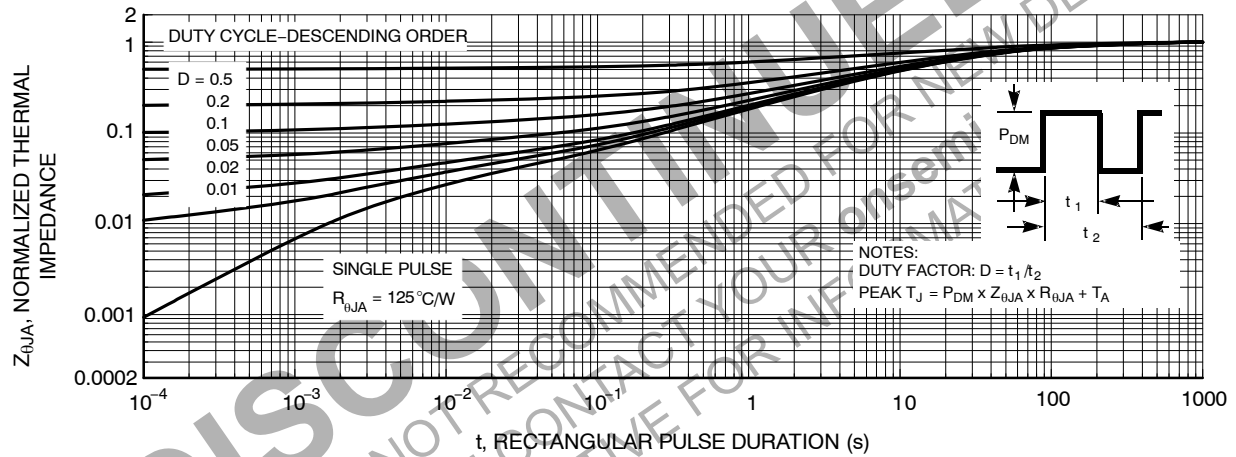


Figure 14. Transient Thermal Response Curve

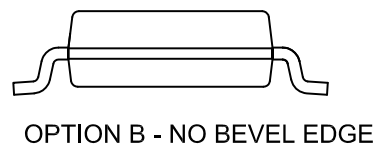
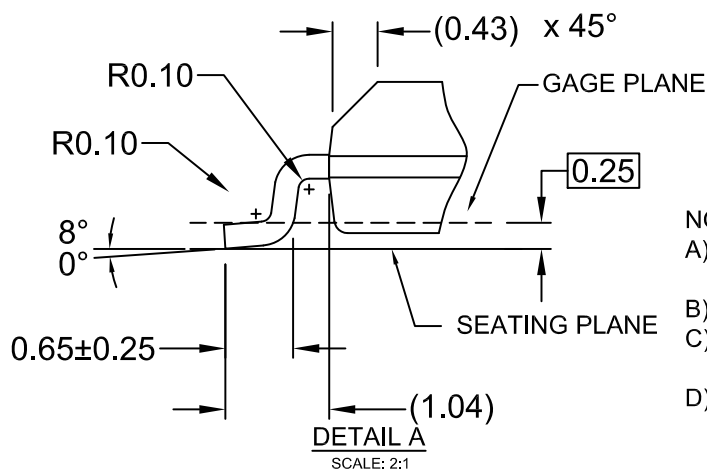
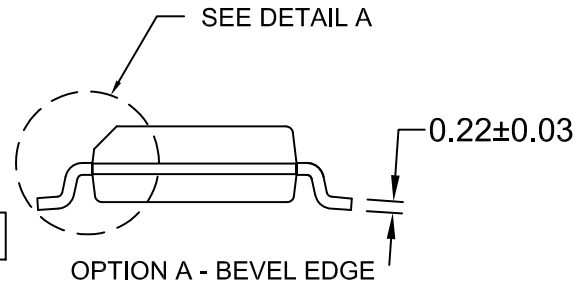
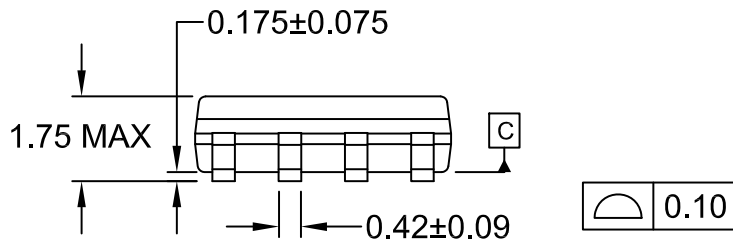
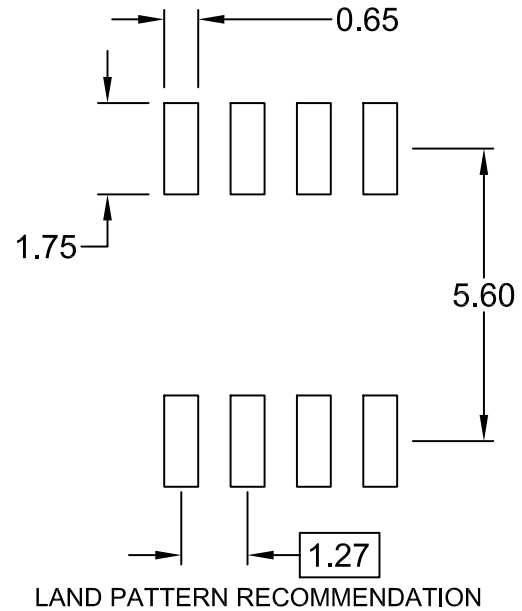
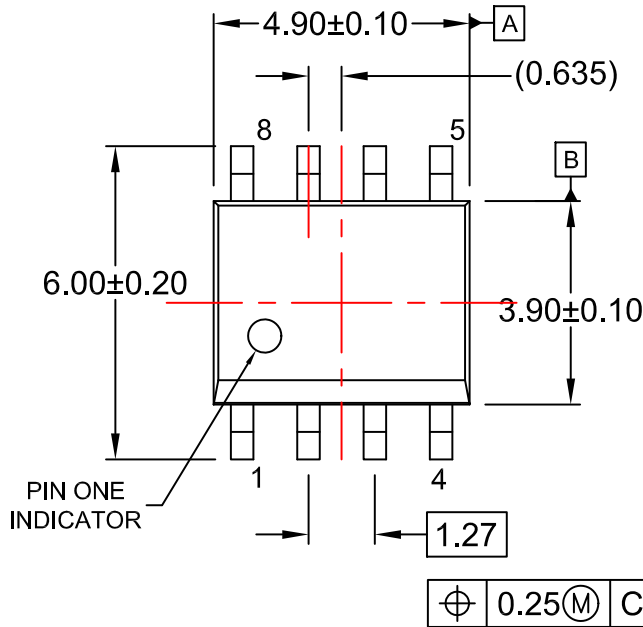
ORDERING INFORMATION

Device	Device Marking	Package Type	Shipping <sup>†</sup>
FDS8817NZ	FDS8817NZ	SOIC8 (Pb-Free)	2500 / Tape & Reel
FDS8817NZ-G	FDS8817NZ	SOIC8 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**SOIC8**  
**CASE 751EB**  
**ISSUE A**

DATE 24 AUG 2017



**NOTES:**

- A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
- D) LANDPATTERN STANDARD: SOIC127P600X175-8M

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